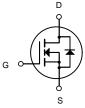


# **Description**

The HRE1L002SNTL uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

# SOT-523

(SC-89)



#### N-Channel MOSFET

#### **General Features**

 $V_{DS} = 60V I_D = 0.115A$ 

 $R_{DS(ON)}$  < 3  $\Omega$ @  $V_{GS}$ =10V

#### **Application**

Battery protection

Load switch

Uninterruptible power supply

#### **Package Marking and Ordering Information**

| Product ID   | Pack           | Marking | Qty(PCS) |
|--------------|----------------|---------|----------|
| HRE1L002SNTL | SOT-523(SC-89) | 72K     | 3000     |

#### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

| Symbol         | Parameter  | Limit      | Unit       |
|----------------|--|------------|------------|
| VDS            | Drain-Source Voltage                             | 60         | V          |
| Vgs            | Gate-Source Voltage                              | ±20        | V          |
| I <sub>D</sub> | Drain Current-Continuous                         | 0.115      | А          |
| P <sub>D</sub> | Maximum Power Dissipation                        | 0.15       | W          |
| Тл,Твтв        | Operating Junction and Storage Temperature Range | -55 To 150 | $^{\circ}$ |
| ReJA           | Thermal Resistance,Junction-to-Ambient (Note 2)  | 833        | °C/W       |



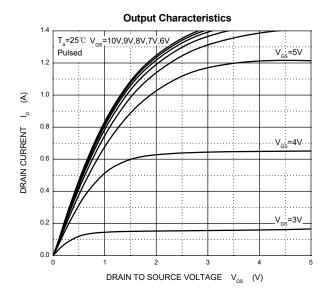
# Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

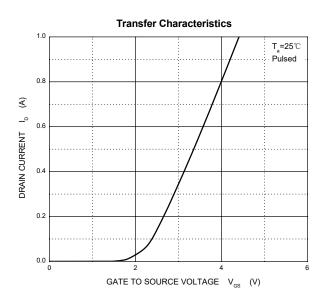
| Parameter                       | Symbol              | Test conditions   | Min  | Тур | Max   | Unit |
|---------------------------------|---------------------|---|------|-----|-------|------|
| Drain-Source Breakdown Voltage  | $V_{(BR)DSS}$       | V <sub>GS</sub> =0 V, I <sub>D</sub> =250 μA              | 60   |     |       | V    |
| Gate-Threshold Voltage          | V <sub>th(GS)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 μA | 1    |     | 2.5   |      |
| Gate-body Leakage               | I <sub>GSS</sub>    | V <sub>DS</sub> =0 V, V <sub>GS</sub> =±20 V              |      |     | ±80   | nA   |
| Zero Gate Voltage Drain Current | I <sub>DSS</sub>    | V <sub>DS</sub> =60 V, V <sub>GS</sub> =0 V               |      |     | 80    | nA   |
| On-state Drain Current          | I <sub>D(ON)</sub>  | V <sub>GS</sub> =10 V, V <sub>DS</sub> =7 V               | 500  |     |       | mA   |
| Drain-Source On-Resistance      | В                   | V <sub>GS</sub> =10 V, I <sub>D</sub> =115mA              |      | 1.3 | 3     | Ω    |
| Diam-Source On-Resistance       | R <sub>DS(on)</sub> | V <sub>GS</sub> =4.5V, I <sub>D</sub> =50mA               |      | 2   | 5     |      |
| Forward Trans conductance       | g <sub>fs</sub>     | V <sub>DS</sub> =10 V, I <sub>D</sub> =200mA              | 80   |     |       | ms   |
| Drain course on voltage         |                     | V <sub>GS</sub> =10V, I <sub>D</sub> =500mA               |      |     | 3.75  | V    |
| Drain-source on-voltage         | V <sub>DS(on)</sub> | V <sub>GS</sub> =5V, I <sub>D</sub> =50mA                 |      |     | 0.375 | V    |
| Diode Forward Voltage           | V <sub>SD</sub>     | I <sub>S</sub> =115mA, V <sub>GS</sub> =0 V               | 0.55 |     | 1.2   | V    |
| Input Capacitance               | C <sub>iss</sub>    | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz         |      |     | 50    |      |
| Output Capacitance              | C <sub>oss</sub>    |   |      |     | 25    | pF   |
| Reverse Transfer Capacitance    | C <sub>rss</sub>    |   |      |     | 5     |      |

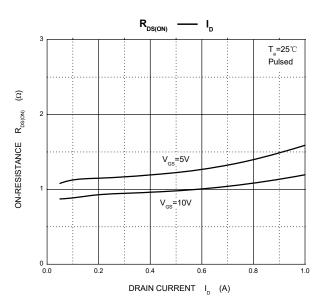
#### **Switching Time**

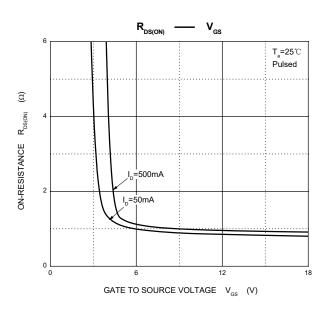
| Turn-on Time  | t <sub>d(on)</sub> | V <sub>DD</sub> =25 V, R <sub>L</sub> =50Ω       |  | 20 | no |
|---------------|--------------------|--|--|----|----|
| Turn-off Time | $t_{d(off)}$       | $I_D$ =500mA, $V_{GEN}$ =10 V $R_G$ =25 $\Omega$ |  | 40 | ns |

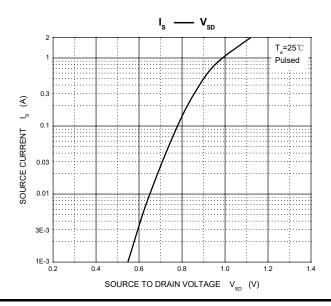
# **Typical Characteristics**





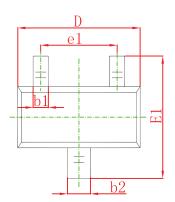


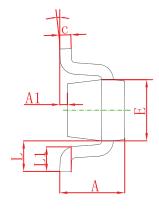


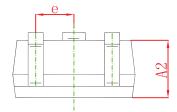




# SOT-523(SC-89) Package Information

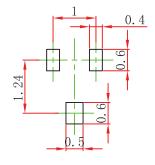






| Symbol | Dimensions | In Millimeters | Dimensions In Inches |       |  |
|--------|------------|----------------|----------------------|-------|--|
|        | Min.       | Max.           | Min.                 | Max.  |  |
| Α      | 0.700      | 0.900          | 0.028                | 0.035 |  |
| A1     | 0.000      | 0.100          | 0.000                | 0.004 |  |
| A2     | 0.700      | 0.800          | 0.028                | 0.031 |  |
| b1     | 0.150      | 0.250          | 0.006                | 0.010 |  |
| b2     | 0.250      | 0.350          | 0.010                | 0.014 |  |
| С      | 0.100      | 0.200          | 0.004                | 0.008 |  |
| D      | 1.500      | 1.700          | 0.059                | 0.067 |  |
| E      | 0.700      | 0.900          | 0.028                | 0.035 |  |
| E1     | 1.450      | 1.750          | 0.057                | 0.069 |  |
| е      | 0.500 TYP. |                | 0.020 TYP.           |       |  |
| e1     | 0.900      | 1.100          | 0.035                | 0.043 |  |
| L      | 0.400      | REF.           | 0.016 REF.           |       |  |
| L1     | 0.260      | 0.460          | 0.010                | 0.018 |  |
| θ      | 0°         | 8°             | 0°                   | 8°    |  |

# SOT-523(SC-89) Suggested Pad Layout



#### Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.



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